捷多邦,专业PCB打样工厂,24小时加急**SM74LVC1G57**CONFIGURABLE MULTIPLE-FUNCTION GATE

SCES414G - NOVEMBER 2002 - REVISED SEPTEMBER 2003

- Available in the Texas Instruments
 NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 6.3 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA
 Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DBV OR DCK PACKAGE (TOP VIEW)



YEA, YEP, YZA OR YZP PACKAGE (BOTTOM VIEW)

			1
		40	
GND	02	50	Vcc
ln1	01	60	ln2

description/ordering information

This configurable multiple-function gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G57 features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XNOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

This device functions as an independent gate, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

TA	PACKAGET		PACKAGET		ORDERABLE PART NUMBER	TOP-SIDE MARKING‡
Let It	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA		SN74LVC1G57YEAR			
TH !-	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)	T	SN74LVC1G57YZAR			
−40°C to 85°C	NanoStar [™] – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Tape and reel	SN74LVC1G57YEPR	CL_		
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	人性	SN74LVC1G57YZPR	50-		
	SOT (SOT-23) – DBV	Tape and reel	SN74LVC1G57DBVR	CA7_		
	SOT (SC-70) – DCK	Tape and reel	SN74LVC1G57DCKR	CL_		

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.

YEA/YZA,YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, ● = Pb-free).

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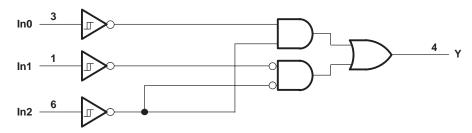
description/ordering information (continued)

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE

	INPUTS	OUTPUT	
ln2	ln1	In0	Y
L	L	L	Н
L	L	Н	L
L	Н	L	Н
L	Н	Н	L
Н	L	L	L
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	Н

logic diagram (positive logic)





FUNCTION SELECTION TABLE

LOGIC FUNCTION	FIGURE NO.
2-input AND	1
2-input AND with both inputs inverted	4
2-input NAND with inverted input	2, 3
2-input OR with inverted input	2, 3
2-input NOR	4
2-input NOR with both inputs inverted	1
2-input XNOR	5

logic configurations

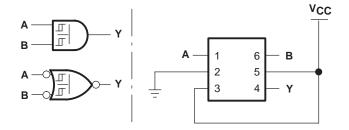


Figure 1. 2-Input AND Gate

A — III — Y — A — 3 — 4 — Y

Figure 2. 2-Input NAND Gate With Inverted A Input

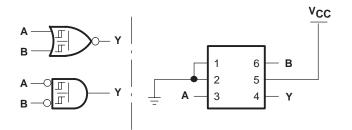


Figure 3. 2-Input NAND Gate With Inverted B Input

Figure 4. 2-Input NOR Gate

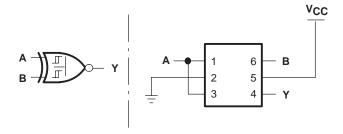


Figure 5. 2-Input XNOR Gate



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Supply voltage range, V_{CC}
(see Note 1)
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2)

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
.,	0 1 1	Operating	1.65	5.5	.,	
VCC	Supply voltage	Data retention only	1.5		V	
٧ı	Input voltage		0	5.5	V	
VO	Output voltage		0	Vcc	V	
		V _{CC} = 1.65 V		-4		
	IOH High-level output current	V _{CC} = 2.3 V		-8		
loh		V _{CC} = 3 V		-16	mA	
				-24		
		V _{CC} = 4.5 V		-32		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8]	
loL	Low-level output current	., .,	16		mA	
		VCC = 3 V		24		
		V _{CC} = 4.5 V		32		
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONI	DITIONS	VCC	MIN	TYP [†]	MAX	UNIT
			1.65 V	0.79		1.16	
V _{T+}		2.3 V	1.11		1.56		
Positive-going input threshold			3 V	1.5		1.87	V
voltage			4.5 V	2.16		2.74	
			5.5 V	2.61		3.33	
			1.65 V	0.39		0.62	
V _T -			2.3 V	0.58		0.87	
Negative-going input threshold			3 V	0.84		1.14	V
voltage			4.5 V	1.41		1.79	
			5.5 V	1.87		2.29	
			1.65 V	0.37		0.62	
ΔV_{T}			2.3 V	0.48		0.77	
Hysteresis		3 V	0.56		0.87	V	
$(V_{T+} - V_{T-})$			4.5 V	0.71		1.04	
			5.5 V	0.71		1.11	
	I _{OH} = -100 μA		1.65 V to 5.5 V	V _{CC} -0.1			
	$I_{OH} = -4 \text{ mA}$		1.65 V	1.2			
	$I_{OH} = -8 \text{ mA}$		2.3 V	1.9			
VOH	$I_{OH} = -16 \text{ mA}$		6.17	2.4			V
	I _{OH} = -24 mA		3 V	2.3			
	$I_{OH} = -32 \text{ mA}$		4.5 V	3.8			
	I _{OL} = 100 μA		1.65 V to 5.5 V			0.1	
	I _{OL} = 4 mA		1.65 V			0.45	
	I _{OL} = 8 mA		2.3 V			0.3	
VOL	I _{OL} = 16 mA		6.17			0.4	V
	I _{OL} = 24 mA		3 V			0.55	
	I _{OL} = 32 mA		4.5 V			0.55	
II	V _I = 5.5 V or GND		0 to 5.5 V			±1	μΑ
l _{off}	V _I or V _O = 5.5 V		0			±10	μΑ
lcc	$V_I = 5.5 \text{ V or GND},$	I _O = 0	1.65 V to 5.5 V			10	μΑ
ΔICC	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μΑ
Ci	V _I = V _{CC} or GND		3.3 V		3.5		pF

 $[\]dagger$ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

PARAMETER	METER FROM TO (OUTPUT		V _{CC} = ± 0.1		± 0.2		± 0.3		÷ 0.9		UNIT
		(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	Any In	Y	3.2	14.4	2	8.3	1.5	6.3	1.1	5.1	ns

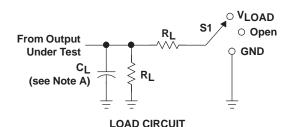


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operating characteristics, $T_A = 25^{\circ}C$

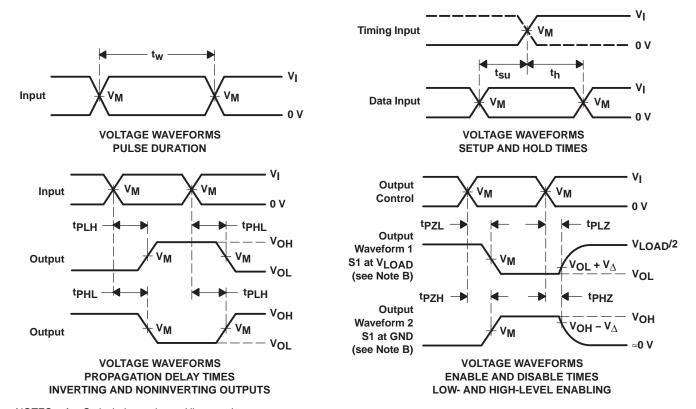
PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
		CONDITIONS	TYP	TYP TYP		TYP	UNII
C _{pd}	Power dissipation capacitance	f = 10 MHz	20	20	21	22	pF

PARAMETER MEASUREMENT INFORMATION



TEST	S1
tpLH/tpHL	Open
tPLZ/tPZL	VLOAD
tPHZ/tPZH	GND

.,	INI	PUTS	.,	.,		_	.,
VCC	VI	t _r /t _f	VM	VLOAD	CL	RL	$v_{\!\scriptscriptstyle \Delta}$
1.8 V \pm 0.15 V	VCC	≤2 ns	V _{CC} /2	2×VCC	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	VCC	≤2 ns	V _{CC} /2	2×VCC	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	VCC	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

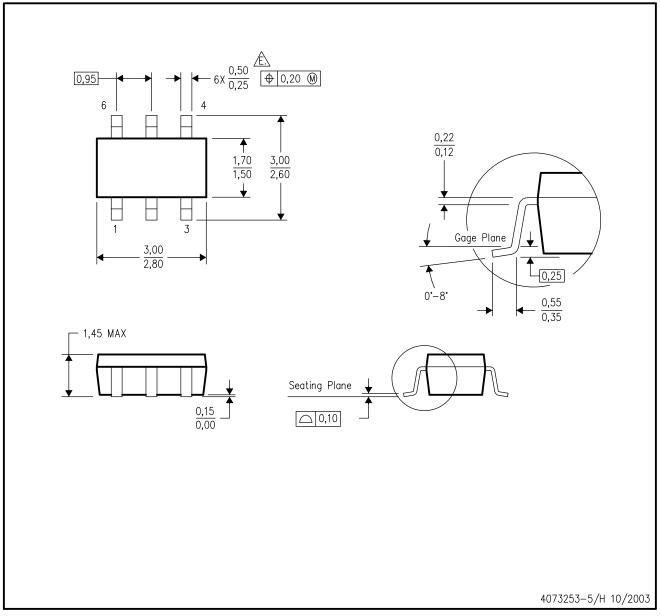
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω .
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms



DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

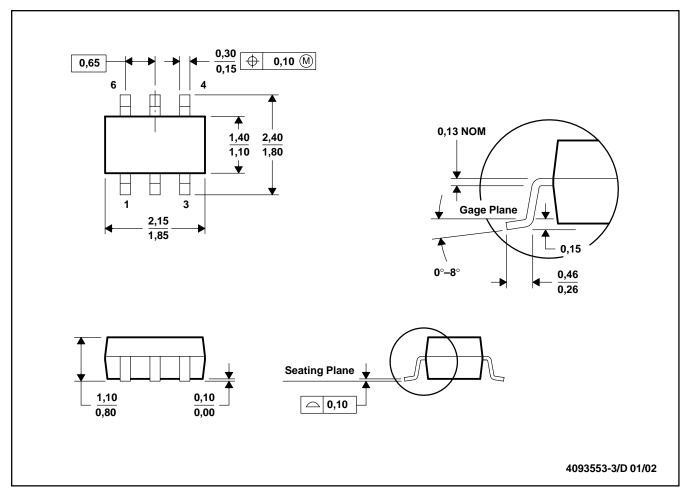
- A. All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.

 D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE

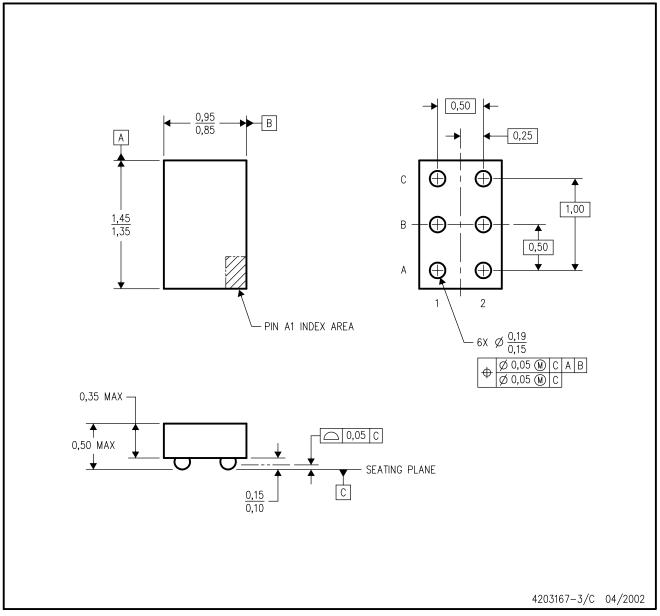


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-203

YEA (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



NOTES:

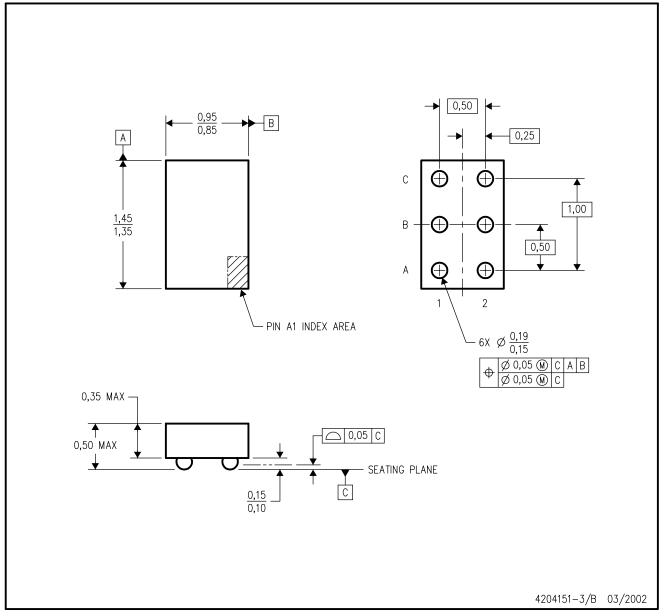
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. NanoStar™ package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is tin-lead (SnPb). Refer to the 6 YZA package (drawing 4204151) for lead-free.

NanoStar is a trademark of Texas Instruments.



YZA (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



NOTES:

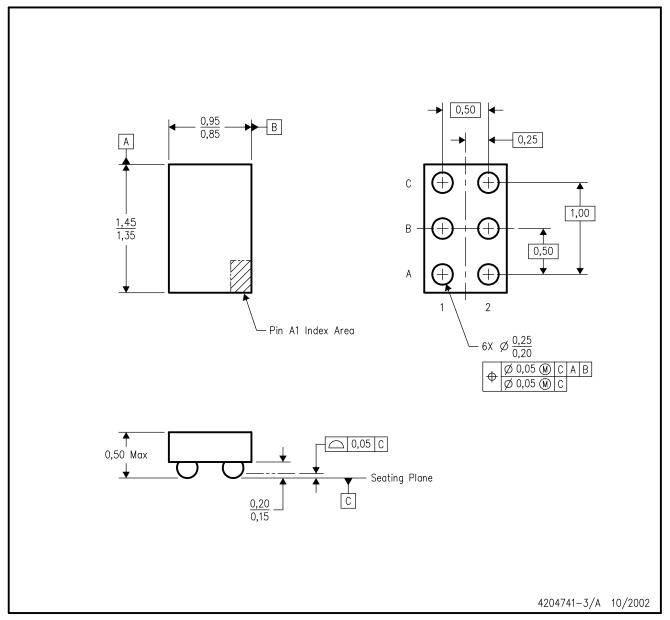
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is lead-free. Refer to the 6 YEA package (drawing 4203167) for tin-lead (SnPb).

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YZP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



NOTES:

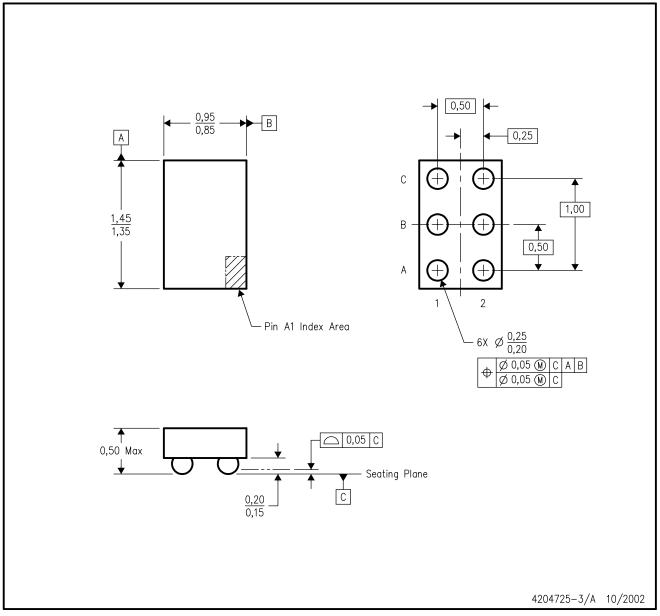
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 6 YEP package (drawing 4204725) for tin-lead (SnPb).

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YEP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. NanoStar™ package configuration.
- D. This package is tin-lead (SnPb). Refer to the 6 YZP package (drawing 4204741) for lead-free.

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